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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Group Art Unit: 2813
Examiner: Gene M. Munson
Confirmation No.: 2155

In Re PATENT APPLICATION of:

Applicant(s): Hirotaka KOMATSUBARA)
Serial No.: 10/765,156)
Filing Date: January 28, 2004) AMENDMENT
For: METHOD FOR MANUFACTURING SOI)
LOCOS MOSFET WITH METAL OXIDE)
FILM OR IMPURITY-IMPLANTED FIELD)
OXIDE (as amended))
Atty. Docket: KAN 155)

May 31, 2005

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

This paper is in response to the Official Action mailed on March 1, 2005. No fee is due. However, please charge our Deposit Account No. 18-0002 if any fees are needed to enter this paper, and please advise us accordingly. It is noted that no petition is required because of the authorization to charge, but please consider this paper a petition for extension of time if needed.

The amendments to claims 5 and 9 are supported in the drawing and at page 5 of the specification, 7th through 4th lines from the bottom.

New claims 14-15 are supported in original claim 1; page 4, line 14; and Figs. 2D and 3B. The specification is amended to support the lexicography "inclined edge" in the new claims. As to "generally perpendicular," an enlargement of Fig. 3C is attached, showing that the direction of the ion implantation (the line of the arrows) is generally perpendicular to the inclined edge of the silicon layer 230; the Applicant measured the angle on the sketch to be 81°, using a protractor.

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